



#### **60V P-CHANNEL ENHANCEMENT MODE MOSFET POWERDI**

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C		
-60V	$25m\Omega$ @ $V_{GS} = -10V$	-7.7A		
	$33m\Omega$ @ $V_{GS} = -4.5V$	-6.8A		

#### **Features and Benefits**

- Low R<sub>DS(ON)</sub> ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Description and Applications**

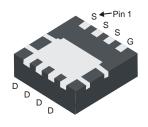
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- Backlighting
- **Power Management Functions**
- DC-DC Converters

#### **Mechanical Data**

- Case: POWFRDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

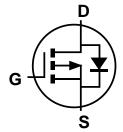
#### POWERDI®3333-8



**Bottom View** 



Top View



**Equivalent Circuit** 

### **Ordering Information** (Note 5)

Part Number	Case	Packaging
DMP6023LFGQ-7	POWERDI®3333-8	2,000/Tape & Reel
DMP6023LFGQ-13	POWERDI®3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



P23 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 13 = 2013) WW = Week Code (01 ~ 53)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Durin Courset (Note 7) // 40//	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-7.7 -6.2	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-10.3 -8.2	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	-55	Α
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	-2.2	Α
Avalanche Current, L = 0.1mH			I <sub>AS</sub>	-35.5	А
Avalanche Energy, L = 0.1mH			Eas	62.9	mJ

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	-	Symbol	Value	Units
Total Power Dissipation (Note 6)		$P_{D}$	1.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	123	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ hetaJA}$	69	
Total Power Dissipation (Note 7)		$P_{D}$	2.1	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	D	60	°C/W
Thermal Resistance, Junction to Ambient (Note 1)	t<10s	$R_{\theta JA}$	34	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	6.3	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

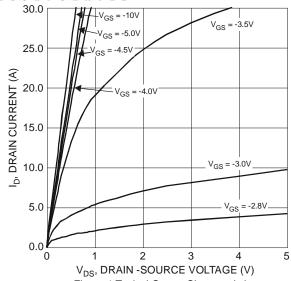
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

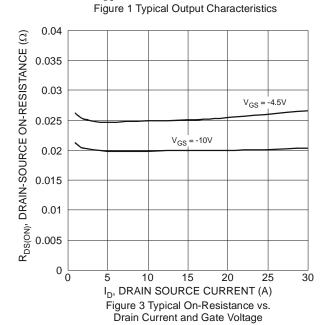
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D	-	_	25	mΩ	$V_{GS} = -10V, I_{D} = -5A$	
Static Dialii-Source Off-Resistance	R <sub>DS(ON)</sub>		_	33	11122	$V_{GS} = -4.5V, I_D = -4A$	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)	•		•	•			
Input Capacitance	C <sub>iss</sub>	I	2569	_	pF	\/ 00\/ \/ 0\/	
Output Capacitance	Coss	_	179	_	pF	$V_{DS} = -30V, V_{GS} = 0V,$ - f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	143	_	pF	I = IIVIMZ	
Gate Resistance	Rg	_	8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	26.5	_	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qq	_	53.1	_	nC	.,	
Gate-Source Charge	Qgs	_	7.1	_	nC	$V_{DS} = -30V, I_{D} = -5A$	
Gate-Drain Charge	$Q_{gd}$	_	12.6	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	7.1	_	ns	$V_{GS} = -10V, V_{DS} = -30V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		110	_	ns	$R_G = 3\Omega$ , $I_D = -5A$	
Turn-Off Fall Time	t <sub>F</sub>	-	62	_	ns	1	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	1	20	_	ns	L 50 di/dt 4000///-	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	14	_	nC	$I_F = -5A$ , di/dt = 100A/ $\mu$ s	

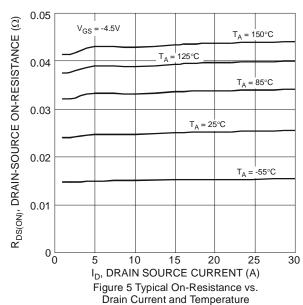
Notes:

- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

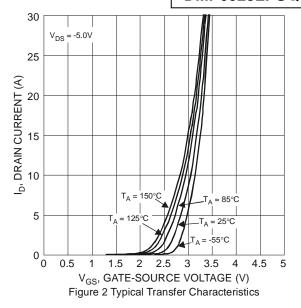


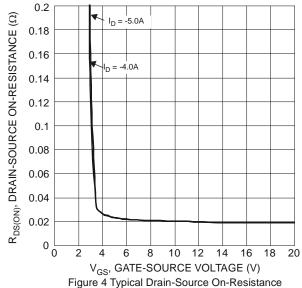






## DMP6023LFGQ

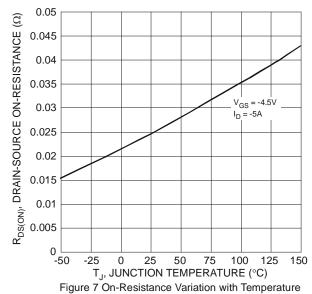


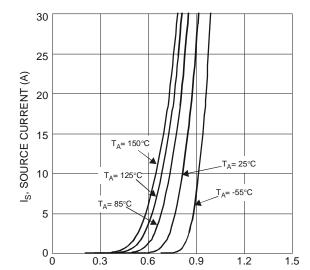


2 1.8 ON-RESISTANCE (NORMALIZED) 1.6 R<sub>DS(ON)</sub>, DRAIN-SOURCE 1.4  $V_{GS} = -4.5V$ 1.2 I<sub>D</sub> = -5A 0.8 0.6 0.4 <u></u> 25 50 75 100 125 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

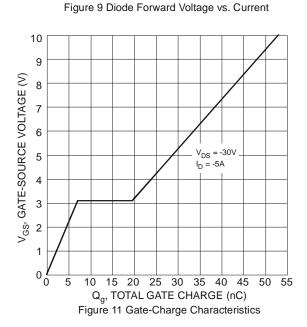
vs. Gate-Source Voltage







V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V)



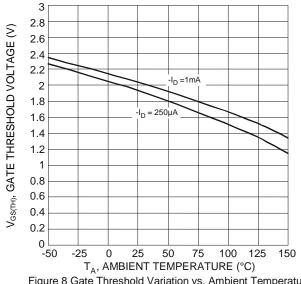
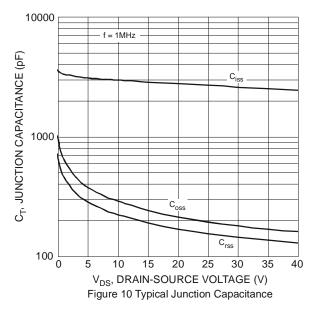
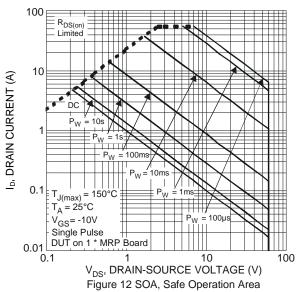
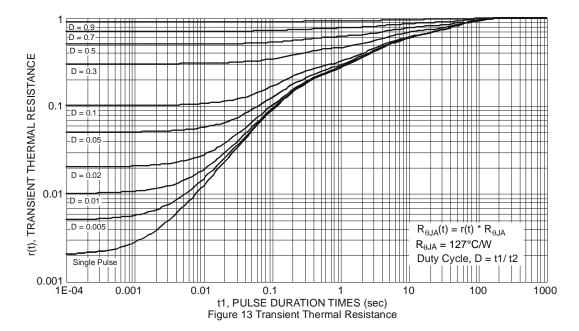


Figure 8 Gate Threshold Variation vs. Ambient Temperature







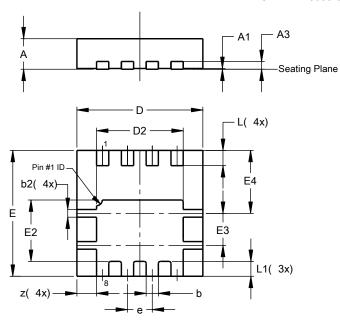




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### POWERDI®3333-8

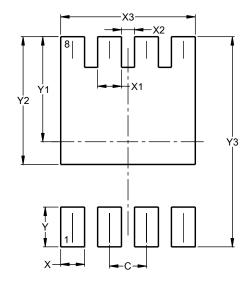


POWERDI®3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
<b>A3</b>	1	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
ם	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	-	-	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### POWERDI®3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700



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